



汕头华汕电子器件有限公司

NPN SILICON TRANSISTOR

**H882**

对应国外型号  
2SD882

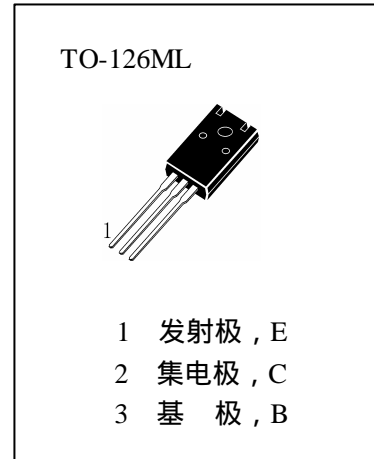
**主要用途**

音频放大、开关功率放大

**极限值** ( $T_a=25$  )

$T_{stg}$	— 贮存温度.....	-55~150
$T_j$	— 结温.....	150
$P_C$	— 集电极功率耗散 ( $T_c=25$ ) .....	10W
$P_C$	— 集电极功率耗散 ( $T_A=25$ ) .....	1W
$V_{CBO}$	— 集电极—基极电压.....	40V
$V_{CEO}$	— 集电极—发射极电压.....	30V
$V_{EBO}$	— 发射极—基极电压.....	5V
$I_C$	— 集电极电流.....	3A
$I_B$	— 基极电流.....	0.6A

**外形图及引脚排列**



**电参数** ( $T_a=25$  )

参数符号	符号说明	最小值	典型值	最大值	单位	测试条件
$I_{CBO}$	集电极—基极截止电流			1	$\mu A$	$V_{CB}=30V, I_E=0$
$I_{EBO}$	发射极—基极截止电流			1	$\mu A$	$V_{EB}=5V, I_C=0$
$h_{FE}$	直流电流增益	60		400		$V_{CE}=2V, I_C=1A$
$V_{CE(sat)}$	集电极—发射极饱和压降		0.3	0.5	V	$I_C=2A, I_B=0.2A$
$V_{BE(sat)}$	基极—发射极饱和压降		1.0	2	V	$I_C=2A, I_B=0.2A$
$C_{ob}$	输出电容		45		pF	$V_{CB}=10V, I_E=0, f=1MHz$
$f_T$	特征频率		90		MHz	$V_{CE}=5V, I_E=0.1A$

**分档及其标志**

R	O	Y	G
60—120	100—200	160—320	200—400



典型特性曲线

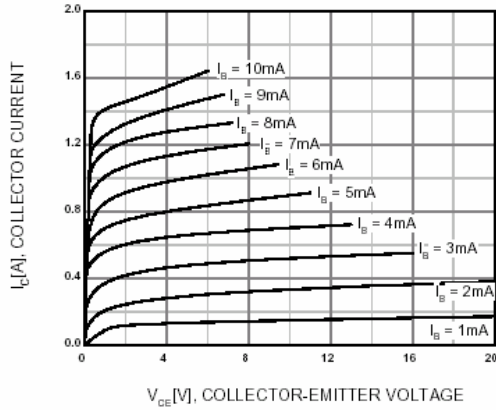


Figure 1. Static Characteristic

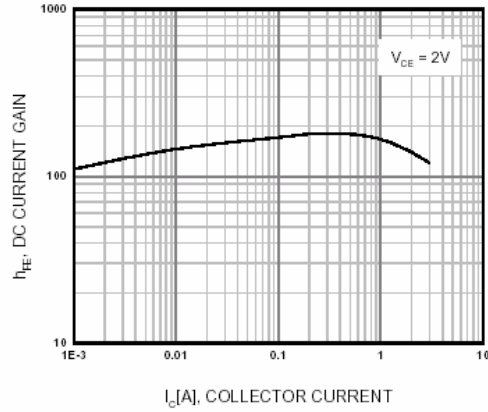


Figure 2. DC current Gain

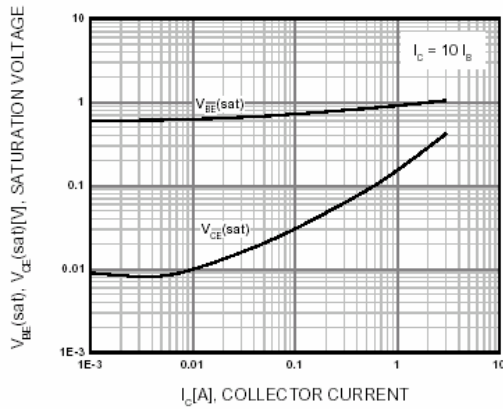


Figure 3. Base-Emitter Saturation Voltage  
Collector-Emmitter Saturation Voltage

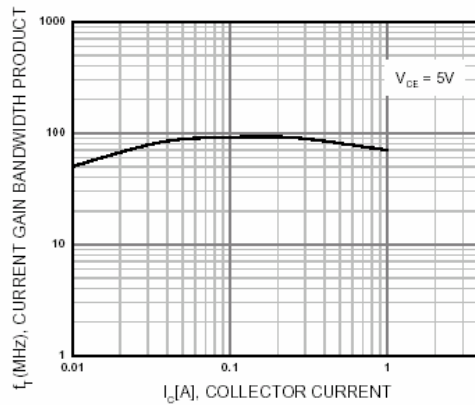


Figure 4. Current Gain Bandwidth Product

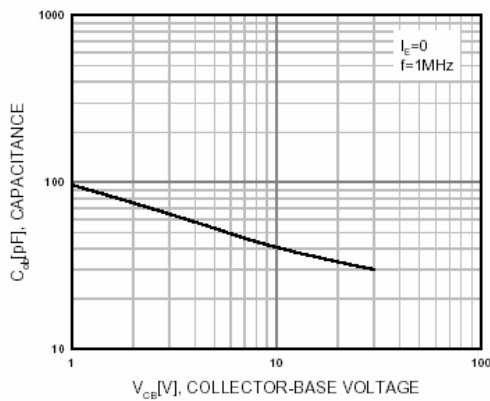


Figure 5. Collector Output Capacitance

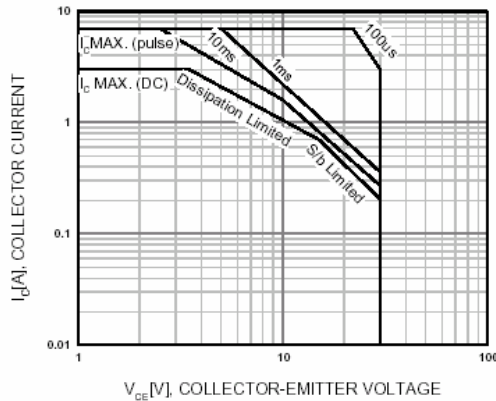


Figure 6. Safe Operating Area



典型特性曲线

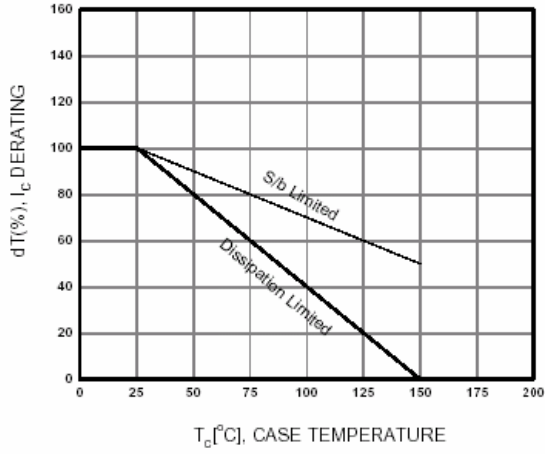


Figure 7. Derating Curve Of Safe Operating Areas

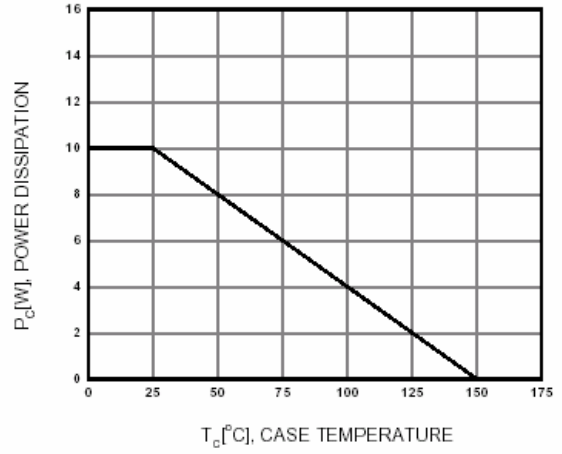


Figure 8. Power Derating